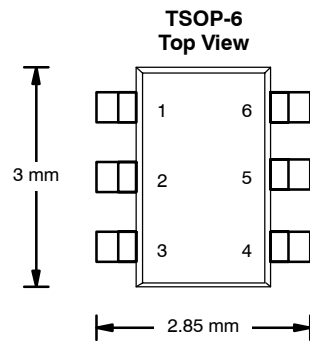


## N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
30	0.060 @ V <sub>GS</sub> = 10 V	4.5
	0.085 @ V <sub>GS</sub> = 4.5 V	3.8

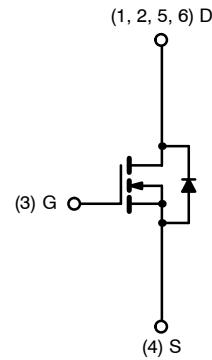
### FEATURES

- TrenchFET® Power MOSFET
- 100% R<sub>g</sub> Tested



Ordering Information: Si3454ADV-T1  
Si3454ADV-T1—E3 (Lead Free)

Marking Code: A4xxx



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 secs	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	4.5	3.4	A
	T <sub>A</sub> = 70 °C		3.6	2.7	
Pulsed Drain Current (10 μs Pulse Width)		I <sub>DM</sub>	20		
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	1.7	1.0	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.0	1.14	
	T <sub>A</sub> = 70 °C		1.3	0.73	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 5 sec	R <sub>thJA</sub>	50	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R <sub>thJF</sub>	30	36	

Notes

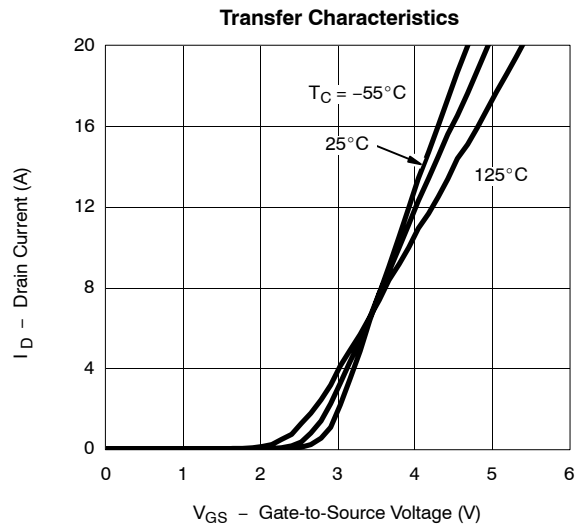
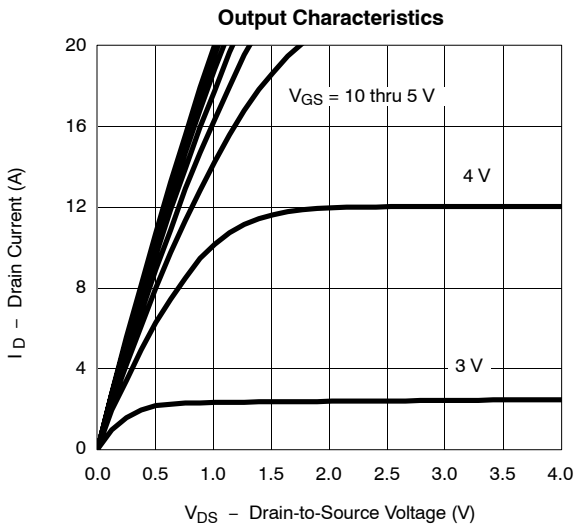
a. Surface Mounted on 1" x 1" FR4 Board.

<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0		3.0	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μA
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C			25	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V	15			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		0.048	0.060	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.8 A		0.070	0.085	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4.5 A		10		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V		0.8	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.5 A		9	15	nC
Gate-Source Charge	Q <sub>gs</sub>			2.5		
Gate-Drain Charge	Q <sub>gd</sub>			1.5		
Gate Resistance	R <sub>g</sub>		0.5		2.9	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ 1 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 6 Ω		10	20	ns
Rise Time	t <sub>r</sub>			10	20	
Turn-Off Delay Time	t <sub>d(off)</sub>			20	35	
Fall Time	t <sub>f</sub>			7	15	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.7 A, di/dt = 100 A/μs		40	80	

**Notes**

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

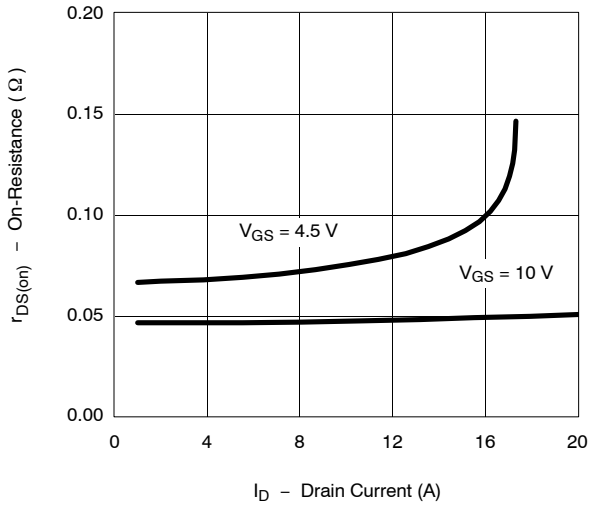
**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



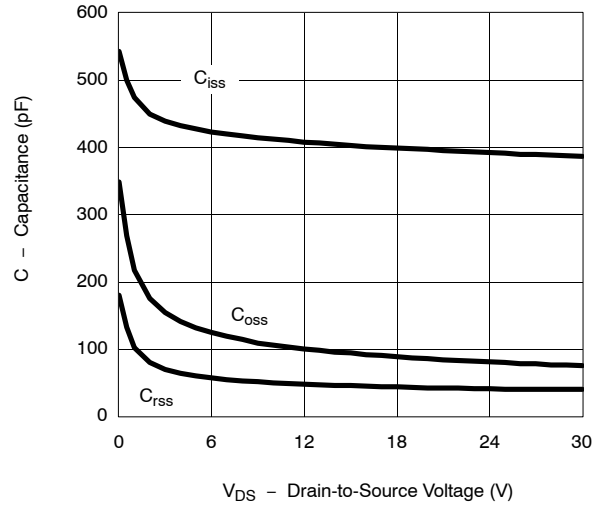


**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

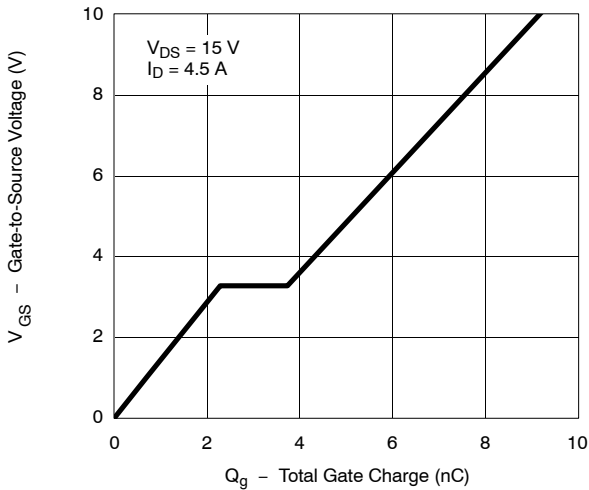
**On-Resistance vs. Drain Current**



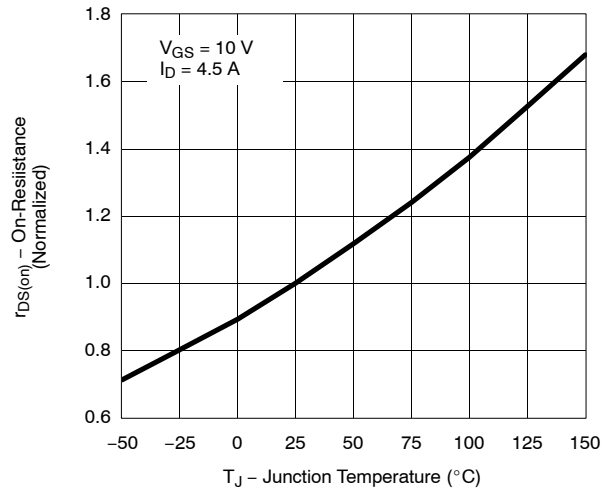
**Capacitance**



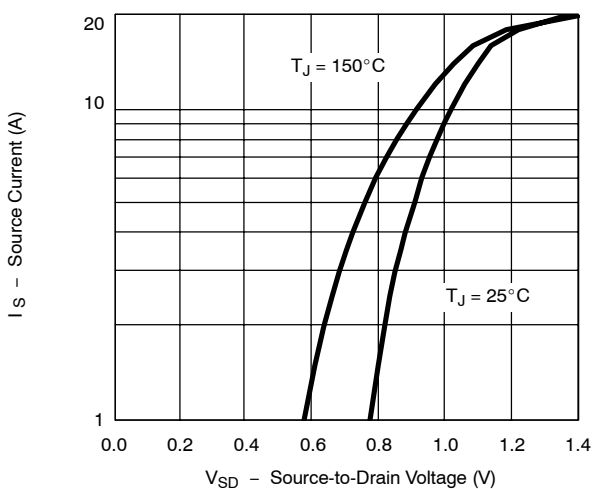
**Gate Charge**



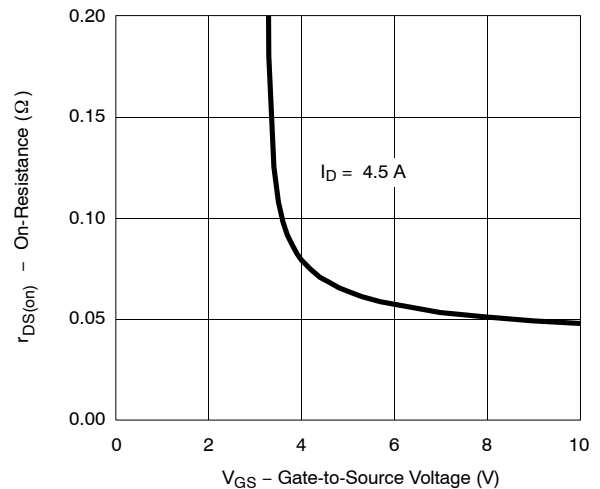
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

